SemTron Microtech Corporation

SMC4240DM

Dual N-Channel MOSFET

■DESCRIPTION

SMC4240DM is the dual N-Channel enhancement mode power field effect transistors are using trench DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance.This device is ideal for load switch applications.

■PART NUMBER INFORMATION

SMC 4240D M - TR G
a b c d e

a : Company name.
b : Product Serial number.
c : Package code M:SOP-8
d : Handling code TR:Tape&Reel
e : Green produce code G:*RoHS Compliant*

■FEATURES

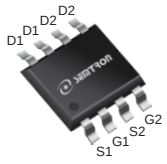
V_{DS}=40V, I_D=8A

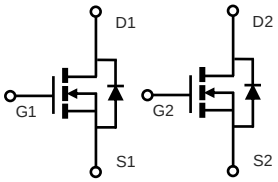
$R_{DS(ON)}$=15mΩ(Typ.)@V_{GS}=10V
$R_{DS(ON)}$=18mΩ(Typ.)@V_{GS}=4.5V

◆100% EAS Guaranteed
◆Improved dv/dt capability
◆High power and current handling capability

■APPLICATIONS

◆Power Management
◆DC/DC Power System
◆Load Switch





SOP-8

■ABSOLUTE MAXIMUM RATINGS (T_A=25°C Unless otherwise noted)

Symbol	Parameter		Rating	Units
V_{DSS}	Drain-Source Voltage		40	V
V_{GSS}	Gate-Source Voltage		±20	V
I_D	Continuous Drain Current (V_{GS}=10V)	T_A=25°C	8	A
		T_A=70°C	6.5	A
I_{DM}	Pulsed Drain Current [B]		32	A
I_{AS}	Avalanche Current [B]		30	A
E_{AS}	Single Pulse Avalanche energy L=0.1mH [B]		45	mJ
P_D	Power Dissipation [A]	T_A=25°C	2	W
		T_A=70°C	1.3	W
T_J	Operation Junction Temperature		-55/150	°C
T_{STG}	Storage Temperature Range		-55/150	°C

■THERMAL RESISTANCE

Symbol	Parameter		Typ	Max	Units
$R_{\theta JA}$	Thermal Resistance Junction to Ambient [A]	t≦10s		62	°C/W
	Thermal Resistance Junction to Ambient [AC]	Steady-State		90	

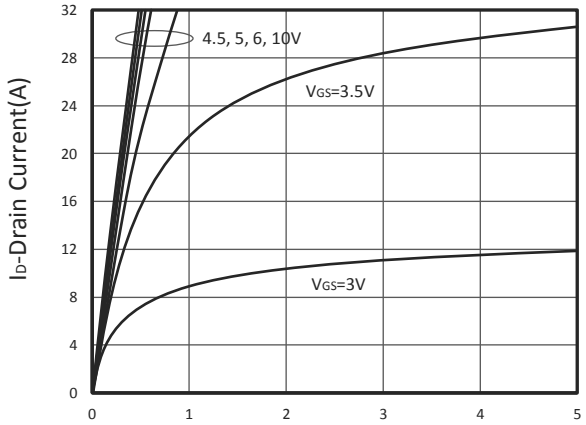
ELECTRICAL CHARACTERISTICS (T_A=25°C Unless otherwise noted)

Symbol	Parameter	Condition	Min	Typ	Max	Unit
Static Parameters						
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V, I_D=250μA	40			V
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS}, I_D=250μA	1.2	1.7	2.5	V
I_{GSS}	Gate Leakage Current	V_{DS}=0V, V_{GS}=±20V			±100	nA
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=40V, V_{GS}=0V, T_J=25°C			1	μA
		V_{DS}=32V, V_{GS}=0V, T_J=75°C			10	
$R_{DS(ON)}$	Drain-source On-Resistance [D]	V_{GS}=10V, I_D=8A V_{GS}=4.5V, I_D=6A		15 18	18 22	mΩ
G_{fs}	Forward Transconductance	V_{DS}=5V, I_D=8A		33		S
Diode Characteristics						
V_{SD}	Diode Forward Voltage [D]	I_S=1A, V_{GS}=0V			1	V
I_S	Diode Continuous Forward Current				8	A
t_{rr}	Revese Recovery Time	I_S=8A, dI/dt=100A/μs		10		ns
Q_{rr}	Reverse Recovery Charge			3.5		nC
Dynamic and Switching Parameters [E]						
Q_g	Total Gate Charge	V_{DS}=20V, V_{GS}=10V, I_D=8A		24.8	30.1	nC
Q_g	Total Gate Charge (4.5V)			11.8	13.9	
Q_{gs}	Gate-Source Charge			3.6	4.3	
Q_{gd}	Gate-Drain Charge			4.7	6.6	
C_{iss}	Input Capacitance	V_{DS}=20V,V_{GS}=0V, f=1MHz		1110	1430	pF
C_{oss}	Output Capacitance			108	141	
C_{rss}	Reverse Transfer Capacitance			82	115	
R_g	Gate Resistance	V_{GS}=0V, V_{DS}=0V, F=1MHz		2.5		
$t_{d(on)}$	Turn-On Time	V_{DD}=20V, V_{GEN}=10V, R_G=3.3Ω, I_D=1A		7.8	16	nS
t_r				3	6	
$t_{d(off)}$	Turn-Off Time			28	49	
t_f				3.1	5.9	

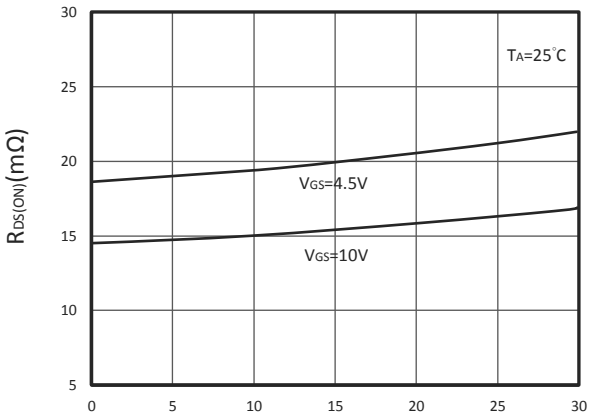
Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged.

A. Surface mounted on FR4 board using 1 in^2 pad size.
B. Pulsed width limited by maximum junction temperature, $T_{J(MAX)}$=150°C (initial temperature T_J=25°C).
C. Using ≤ 10s junction-to-ambient thermal resistance is base on $T_{J(MAX)}$=150°C.
D. Pulse test width ≤300μs and duty cycle ≤ 2%.
E. Guaranteed by design, not subject to production testing.

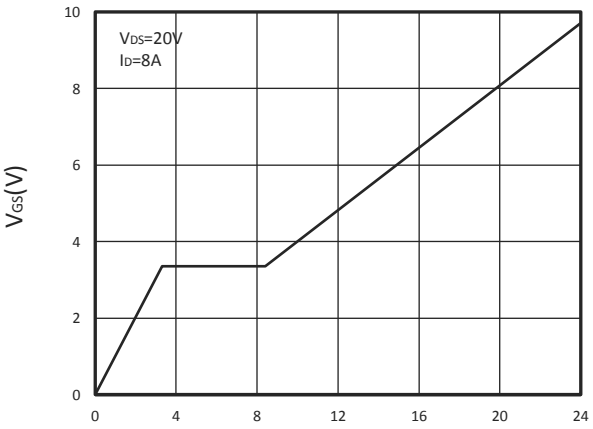
TYPICAL CHARACTERISTICS



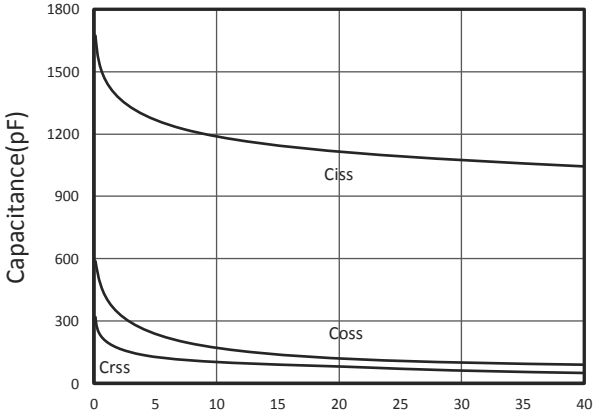
Output Characteristics



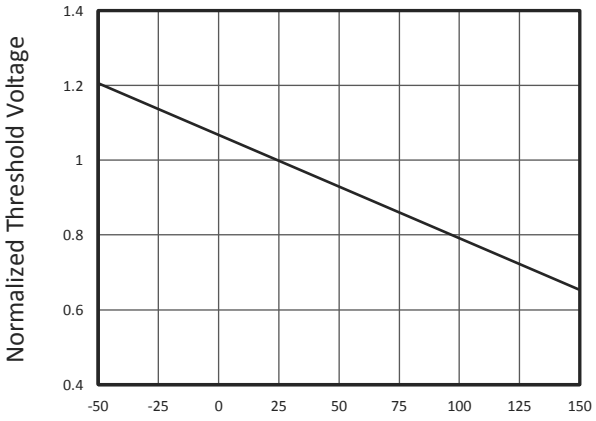
Drain-Source On Resistance



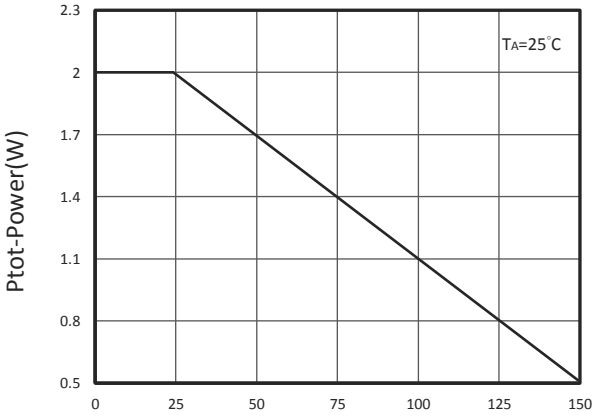
Gate Charge



Capacitance

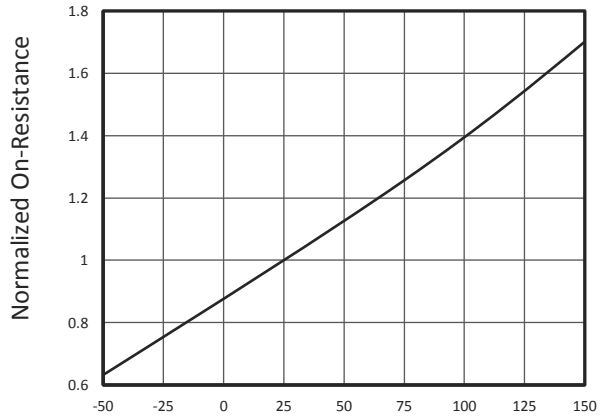


Gate Threshold Voltage

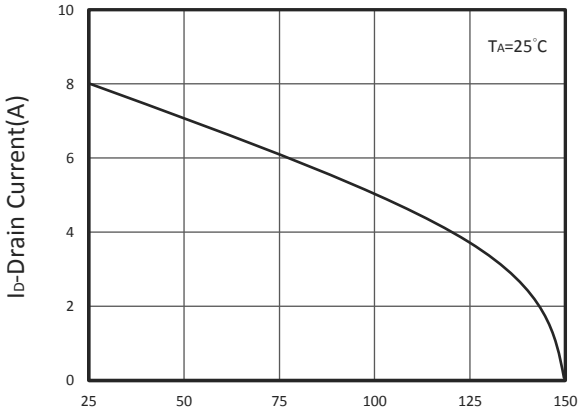


Power Dissipation

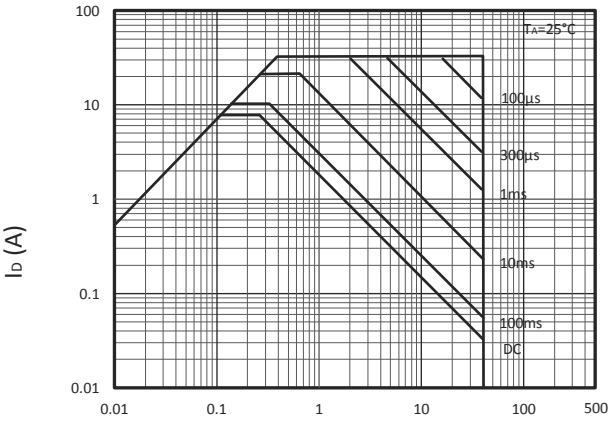
TYPICAL CHARACTERISTICS



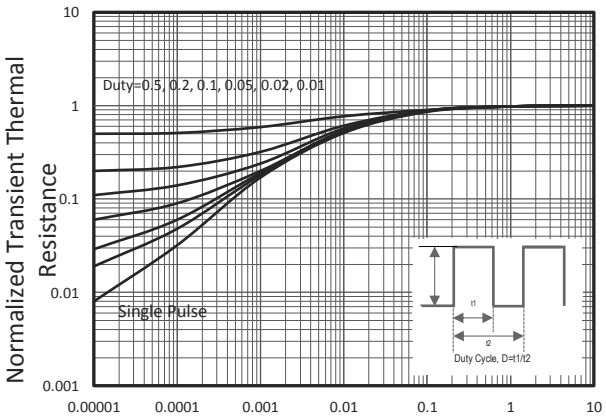
Drain-Source On Resistance



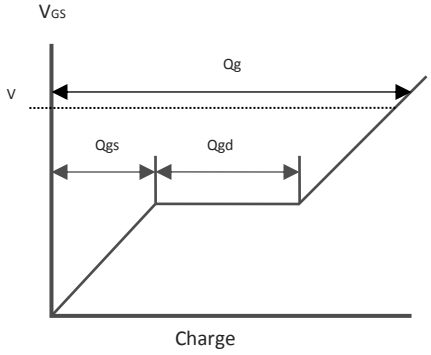
Drain Current vs TJ



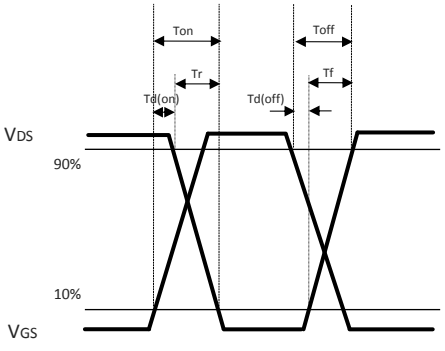
Maximum Safe Operation Area



Thermal Transient Impedance

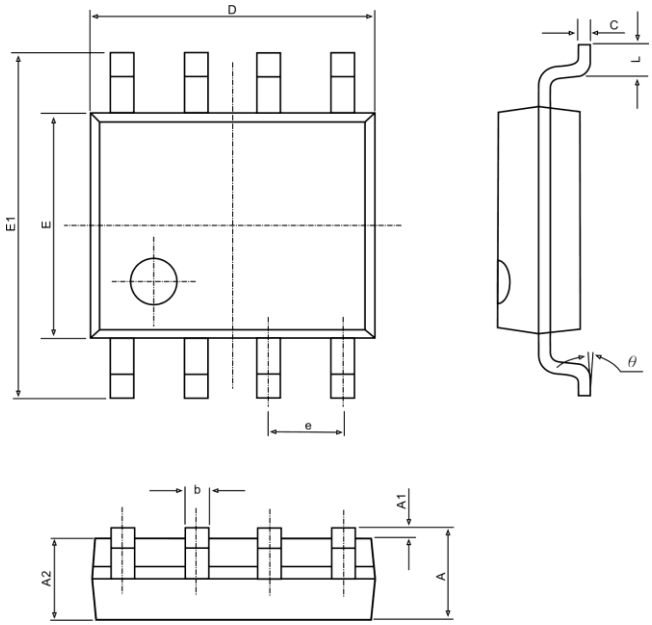


Gate Chrge Waveform

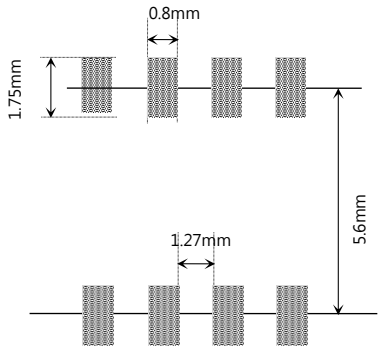


Switching Time Waveform

SOP-8 PACKAGE DIMENSIONS



Recommended Land Pattern



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.300	1.500	0.051	0.059
b	0.390	0.490	0.015	0.019
c	0.200	0.250	0.008	0.010
D	4.800	5.100	0.189	0.201
E	3.800	4.000	0.150	0.157
E1	5.800	6.200	0.228	0.244
e	1.270 BSC		0.050 BSC	
L	0.500	0.800	0.020	0.031
Θ	0°	8°	0°	8°